HALOGEN

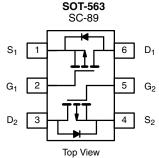
FREE





Dual P-Channel 20 V (D-S) MOSFET

PRODUCT SUMMARY			
V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (mA)	
- 20	1.2 at V _{GS} = - 4.5 V	- 350	
	1.6 at V _{GS} = - 2.5 V	- 300	
	2.7 at V _{GS} = - 1.8 V	- 150	



Marking Code: B

Ordering Information: Si1023X-T1-GE3 (Lead (Pb)-free and Halogen-free)

FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET® Power MOSFET: 1.8 V Rated
- Very Small Footprint
- · High-Side Switching
- Low On-Resistance: 1.2 Ω
- Low Threshold: 0.8 V (typ.)
- · Fast Switching Speed: 14 ns
- 1.8 V Operation
- Gate-Source ESD Protected: 2000 V
- Compliant to RoHS Directive 2002/95/EC

BENEFITS

- · Ease in Driving Switches
- · Low Offset (Error) Voltage
- Low-Voltage Operation
- High-Speed Circuits
- · Low Battery Voltage Operation

APPLICATIONS

- Drivers: Relays, Solenoids, Lamps, Hammers, Displays, Memories
- Battery Operated Systems
- Power Supply Converter Circuits
- Load/Power Switching Cell Phones, Pagers

ABSOLUTE MAXIMUM RATINGS ($T_A = 25$ °C, unless Parameter		Symbol	5 s	Steady State	Unit
Drain-Source Voltage		V _{DS}	- 20		
Gate-Source Voltage		V _{GS}	± 6		V
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 25 °C	- I _D	- 390	- 370	A
	T _A = 85 °C		- 280	- 265	
Pulsed Drain Current ^b	n Current ^b		- 650		mA
Continuous Source Current (Diode Conduction) ^a		I _S	- 450	- 450 - 380	
Maximum Power Dissipation ^a	T _A = 25 °C	P _D	280	250	mW
	T _A = 85 °C		145	130	
Operating Junction and Storage Temperature Rar	nge	T _J , T _{stg} - 55 to 150		°C	
Gate-Source ESD Rating (HBM, Method 3015)		ESD	2000		V

Notes

- a. Surface mounted on FR4 board.
- b. Pulse width limited by maximum junction temperature.

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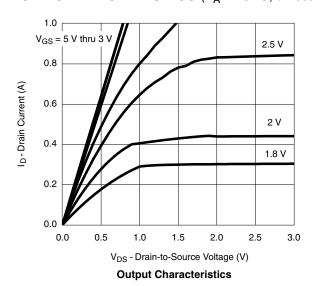
SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)							
Parameter	Symbol	Test Conditions Min.		Тур.	Max.	Unit	
Static							
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	- 0.45			V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 4.5 \text{ V}$		± 1	± 2	μΑ	
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = -16 \text{ V}, V_{GS} = 0 \text{ V}$		- 0.3	- 100	nA	
		V _{DS} = - 16 V, V _{GS} = 0 V, T _J = 85 °C			- 5	μΑ	
On-State Drain Current ^a	I _{D(on)}	V _{DS} = - 5 V, V _{GS} = - 4.5 V	- 700			mA	
Drain-Source On-State Resistance ^a		$V_{GS} = -4.5 \text{ V}, I_D = -350 \text{ mA}$		0.8	1.2	Ω	
	R _{DS(on)}	V _{GS} = - 2.5 V, I _D = - 300 mA		1.2	1.6		
		V _{GS} = - 1.8 V, I _D = - 150 mA		1.8	2.7		
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 10 V, I _D = - 250 mA		0.4		S	
Diode Forward Voltage ^a	V_{SD}	I _S = - 150 mA, V _{GS} = 0 V		- 0.8	- 1.2	V	
Dynamic ^b							
Total Gate Charge	Qg			1500			
Gate-Source Charge	Q_{gs}	$V_{DS} = -10 \text{ V}, V_{GS} = -4.5 \text{ V}, I_{D} = -250 \text{ mA}$		150		рC	
Gate-Drain Charge	Q_{gd}			450		1	
Turn-On Time	t _{d(on)}	V_{DD} = -10 V, R_L = 47 Ω		14		20	
Turn-Off Time	t _{d(off)}	$I_D \cong$ - 200 mA, V_{GEN} = - 4.5 V, R_g = 10 Ω		46		ns	

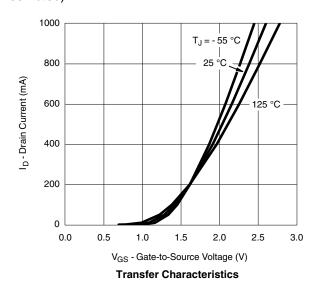
Notes:

- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

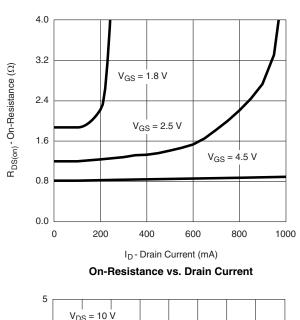


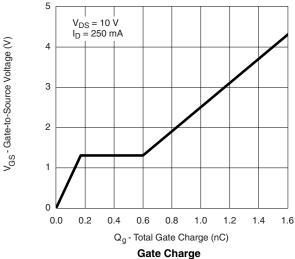


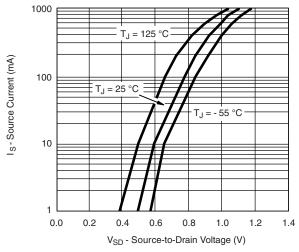




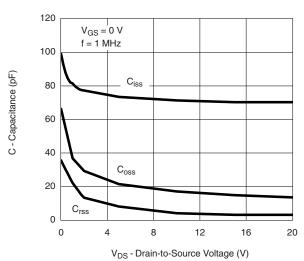
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



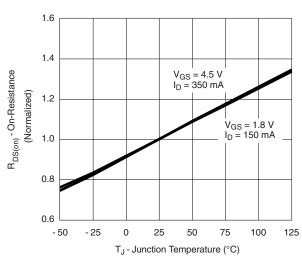




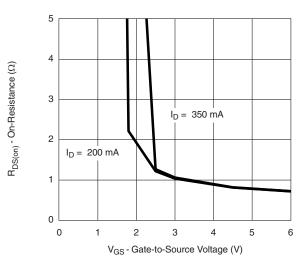
Source-Drain Diode Forward Voltage



Capacitance



On-Resistance vs. Junction Temperature

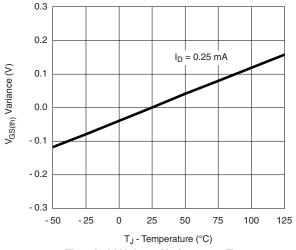


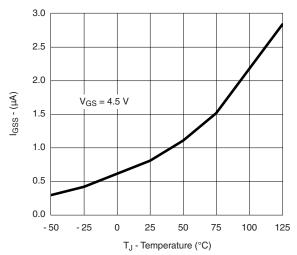
On-Resistance vs. Gate-to-Source Voltage

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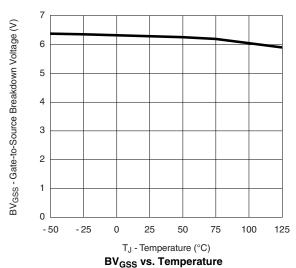
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

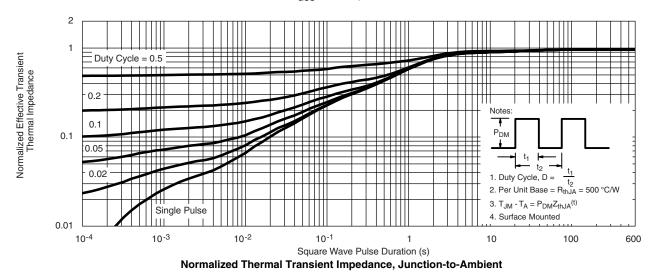




Threshold Voltage Variance vs. Temperature



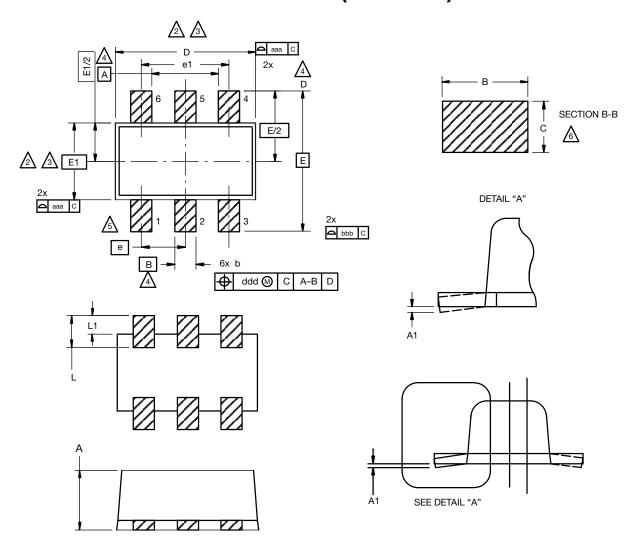




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SC-89 6-Leads (SOT-563F)



Notes

1. Dimensions in millimeters.

Dimension D does not include mold flash, protrusions or gate burrs. Mold flush, protrusions or gate burrs shall not exceed 0.15 mm per dimension E1 does not include interlead flash or protrusion, interlead flash or protrusion shall not exceed 0.15 mm per side.

Dimensions D and E1 are determined at the outmost extremes of the plastic body exclusive of mold flash, the bar burrs, gate burrs and interlead flash, but including any mismatch between the top and the bottom of the plastic body.

ADatums A, B and D to be determined 0.10 mm from the lead tip.

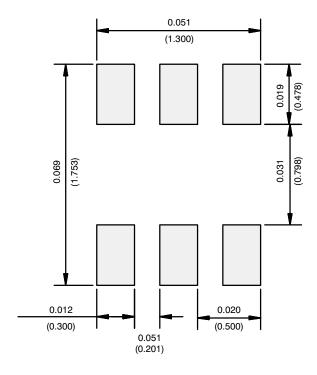
A Terminal numbers are shown for reference only.

These dimensions apply to the flat section of the lead between 0.08 mm and 0.15 mm from the lead tip.

DIM.	MILLIMETERS			
DIW.	MIN.	NOM.	MAX.	
Α	0.56	0.58	0.60	
A1	0	0.02	0.10	
b	0.15	0.22	0.30	
С	0.10	0.14	0.18	
D	1.50	1.60	1.70	
E	1.50	1.60	1.70	
E1	1.15	1.20	1.25	
е	0.45	0.50	0.55	
e1	0.95	1.00	1.05	
L	0.25	0.35	0.50	
L1	0.10	0.20	0.30	
C14-0439-Rev. C, 11-Aug-14 DWG: 5880				



RECOMMENDED MINIMUM PADS FOR SC-89: 6-Lead



Recommended Minimum Pads Dimensions in Inches/(mm)

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APPLICATION NOTE



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